

# **isc Silicon NPN Darlington Power Transistor**

2SD1415

## **DESCRIPTION**

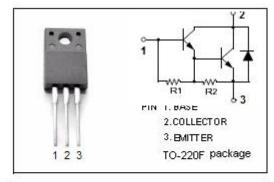
- · Collector-Emitter Breakdown Voltage-
- : V<sub>(BR)CEO</sub>= 100V(Min)
- · Collector-Emitter Saturation Voltage-
  - : V<sub>CE(sat)</sub>= 1.5V(Max) @I<sub>C</sub>= 3A
- · High DC Current Gain
  - : h<sub>FE</sub>= 2000(Min) @ I<sub>C</sub>= 3A, V<sub>CE</sub>= 3V
- Complement to Type 2SB1020
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

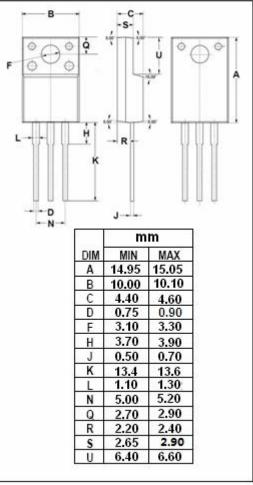
## **APPLICATIONS**

- High power switching applications
- · Hammer driver, pulse motor driver applications



| SYMBOL           | PARAMETER  | VALUE   | UNIT |  |
|------------------|--|---------|------|--|
| V <sub>СВО</sub> | Collector-Base Voltage                                 | 100     | V    |  |
| V <sub>CEO</sub> | Collector-Emitter Voltage                              | 100     | V    |  |
| V <sub>EBO</sub> | Emitter-Base Voltage                                   | 5       | V    |  |
| lc               | Collector Current-Continuous                           | 7       | Α    |  |
| I <sub>B</sub>   | Base Current-Continuous                                | 0.2     | Α    |  |
| Pc               | Collector Power Dissipation<br>@ T <sub>c</sub> =25 °C | 30      | W    |  |
| TJ               | Junction Temperature                                   | 150     | °C   |  |
| T <sub>stg</sub> | Storage Temperature Range                              | -55~150 | °C   |  |







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### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

| SYMBOL                 | PARAMETER                            | CONDITIONS                                 | MIN  | TYP. | MAX   | UNIT       |  |  |
|------------------------|--------------------------------------|--|------|------|-------|------------|--|--|
| V <sub>(BR)</sub> CEO  | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> = 30mA ; I <sub>B</sub> = 0 | 100  |      |       | V          |  |  |
| V <sub>CE(sat)-1</sub> | Collector-Emitter Saturation Voltage | I <sub>C</sub> = 3A; I <sub>B</sub> = 6mA  |      |      | 1.5   | V          |  |  |
| V <sub>CE(sat)-2</sub> | Collector-Emitter Saturation Voltage | I <sub>C</sub> = 7A; I <sub>B</sub> = 14mA |      |      | 2.0   | V          |  |  |
| V <sub>BE(sat)</sub>   | Base-Emitter Saturation Voltage      | I <sub>C</sub> = 3A; I <sub>B</sub> = 6mA  |      |      | 2.5   | V          |  |  |
| I <sub>CBO</sub>       | Collector Cutoff Current             | V <sub>CB</sub> = 100V; I <sub>E</sub> = 0 |      |      | 100   | μ <b>A</b> |  |  |
| I <sub>EBO</sub>       | Emitter Cutoff Current               | V <sub>EB</sub> = 5V; I <sub>C</sub> = 0   |      |      | 3.0   | mA         |  |  |
| h <sub>FE -1</sub>     | DC Current Gain                      | I <sub>C</sub> = 3A; V <sub>CE</sub> = 3V  | 2000 |      | 15000 |            |  |  |
| h <sub>FE -2</sub>     | DC Current Gain                      | I <sub>C</sub> = 7A; V <sub>CE</sub> = 3V  | 1000 |      |       |            |  |  |

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